

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	("6593618").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/06/01 16:09
S2	1520	((257/E27.061) or (257/E27.062) or (257/E27.064)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/06/01 16:10
S3	1520	(257/E27.061 or 257/E27.062 or 257/E27.064).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/01 16:41
S4	1414	(257/E27.061 or 257/E27.062 or 257/E27.064).ccls. and @ad<"20030121"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/01 16:42
S5	126	(257/E27.061 or 257/E27.062 or 257/E27.064).ccls. and @ad<"20030121" and ((gate with (oxide or insulat\$4 or dielectric)) same (halfnium or hf or zirconium or zr or titanium or ti or lanthanum or la or scandium or sc))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/08 12:32
S6	203	(257/E27.061 or 257/E27.062 or 257/E27.064).ccls. and @ad<"20030121" and ((gate with (oxide or insulat\$4 or dielectric)) same (yttrium or Y or lutetium or lu or lawrencium or Ir or vanadium or v or niobium or nb or tantalum or ta or dubnium or db or cesium or ce or praseodymium or pr or neodymium or nd or promethium or pr or samarium or sm or gadolinium or terbium or gd or tb or dysprosium or dy or holmium or ho or erbium or er or thulium or tm or ytterbium or yb or iii or iv or v))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/01 17:36
S7	0	(257/E27.061 or 257/E27.062 or 257/E27.064).ccls. and @ad<"20030121" and ((gate with (oxide or insulat\$4 or dielectric)) same (group adj (iii or iv or v)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/01 17:07
S8	4	(257/E27.061 or 257/E27.062 or 257/E27.064).ccls. and @ad<"20030121" and ((gate with (oxide or insulat\$4 or dielectric)) same (group near4 (iii or iv or v)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/01 17:07

S9	127	(257/E27.061 or 257/E27.062 or 257/E27.064).ccls. and @ad<"20030121" and ((gate with (oxide or insulat\$4 or dielectric)) same (hafnium or hf or zirconium or zr or titanium or ti or lanthanum or la or scandium or sc or rutherfordium or rf))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/01 19:41
S11	1985	257/369.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/01 17:50
S12	1863	257/369.ccls. and @ad<"20030121"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/01 17:51
S13	253	257/369.ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or lanthanum or la or scandium or sc or rutherfordium or rf or yttrium or Y or lutetium or lu or lawrencium or lr or aluminum or al)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/01 18:19
S14	101	257/369.ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (yttrium or Y or lutetium or lu or lawrencium or lr or vanadium or v or niobium or nb or tantalum or ta or dubnium or db or cesium or ce or praseodymium or pr or neodymium or nd or promethium or pr or samarium or sm or gadolinium or terbium or gd or tb or dysprosium or dy or holmium or ho or erbium or er or thulium or tm or ytterbium or yb)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/01 19:41
S15	838	(257/405 or 257/411).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/01 19:41
S16	707	(257/405 or 257/411).ccls. and @ad<"20030121"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/01 19:42

S17	284	(257/405 or 257/411).ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or lanthanum or la or scandium or sc or rutherfordium or rf or yttrium or Y or lutetium or lu or lawrencium or lr or aluminum or al)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/08 16:24
S18	285	(257/405 or 257/411).ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (yttrium or Y or lutetium or lu or lawrencium or lr or vanadium or v or niobium or nb or tantalum or ta or dubnium or db or cesium or ce or praseodymium or pr or neodymium or nd or promethium or pr or samarium or sm or gadolinium or terbium or gd or tb or dysprosium or dy or holmium or ho or erbium or er or thulium or tm or ytterbium or yb or aluminum or al)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 18:08
S22	284	(257/405 or 257/411).ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or lanthanum or la or scandium or sc or rutherfordium or rf or yttrium or Y or lutetium or lu or lawrencium or lr or aluminum or al)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 18:08
S23	41	(257/405 or 257/411).ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (yttrium or Y or lutetium or lu or lawrencium or lr or vanadium or v or niobium or nb or tantalum or ta or dubnium or db or cesium or ce or praseodymium or pr or neodymium or nd or promethium or pr or samarium or sm or gadolinium or terbium or gd or tb or dysprosium or dy or holmium or ho or erbium or er or thulium or tm or ytterbium or yb or aluminum or al))) not S22	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 18:09

S24	5	(257/645 or 257/651).ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or rutherfordium or ru or Sn or tin or Pb or lead or ("iv" near3 (metal or element or compound))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 19:05
S25	2	(257/645 or 257/651).ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (lanthanum or la or scandium or sc or yttrium or Y or lutetium or lu or lawrencium or Ir or actinium or ac or cesium or ce or praseodymium or pr or neodymium or nd or promethium or pm or samarium or sm or gadolinium or gd or terbium or tb or dysprosium or dy or holmium or ho or erbium or er or thulium or tm or ytterbium or yb or ((lanthanoid or lanthanide) near3 (metal or element or compound))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 18:45
S26	39	(257/645 or 257/651).ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (boron or B or aluminum or al or gallium or ga or indium or in or thallium or tl or ("iii" near3 (element or compound))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 18:57
S27	43	(257/645 or 257/651).ccls. and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (vanadium or v or niobium or nb or tantalum or ta or dubnium or db or nitrogen or n or phosphorus or p or arsenic or as or antimony or sb or bismuth or bi or ("v" near3 (metal or element or compound))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 19:00
S28	1663	(c?mos or c?mis or c?mosfet or c?misfet or complementary or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or rutherfordium or ru or Sn or tin or Pb or lead or ("iv" near3 (metal or element or compound))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 19:12

S29	476	(c?mos or c?mis or c?mosfet or c?misfet or (complementary adj (fet or mos or mis or mosfet or misfet)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or rutherfordium or ru or Sn or tin or Pb or lead or ("iv" near3 (metal or element or compound))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 19:13
S30	719	(c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or rutherfordium or ru or Sn or tin or Pb or lead or ("iv" near3 (metal or element or compound))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 19:19
S31	3262	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet).or (p?fet and n?fet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or rutherfordium or ru or Sn or tin or Pb or lead or ("iv" near3 (metal or element or compound))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 19:21

S32	3582	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or rutherfordium or ru or Sn or tin or Pb or lead or ("iv" near3 (metal or element or compound))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 20:10
S33	3537	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or rutherfordium or ru or Sn or tin or Pb or lead or ("iv" near3 (metal or element or compound)))) and (boron or b or gallium or g or indium or in or thallium or tl)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 20:13
S34	3147	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or rutherfordium or ru or Sn or tin or Pb or lead or ("iv" near3 (metal or element or compound)))) and (boron or b or gallium or ga or indium or thallium or tl)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 20:13

S35	825	(cmos or cmosfet or cmis or cmisfet or c?mos or c?mis or c?mosfet or c?misfet or (complementary near3 (fet or mos or mis or mosfet or misfet or transistor)) or (p?mos and n?mos) or (p?mosfet and n?mosfet) or (p?fet and n?fet) or (pmos and nmos) or (pmosfet and nmosfet) or (pfet and nfet)) and @ad<"20030121" and (gate same ((oxide or insulat\$4 or dielectric) with (hafnium or hf or zirconium or zr or titanium or ti or rutherfordium or ru or Sn or tin or Pb or lead or ("iv" near3 (metal or element or compound)))) same (boron or b or gallium or ga or indium or thallium or tl)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 21:43
-----	-----	---	---	----	----	------------------